CLAIMS:

1. Detection circuit for detecting the output power of a power amplifier, comprising:

- a first current mirror transistor (T11) having a base, which is connectable to a power transistor (T10), and a collector;

- a RF detection means (RF-det) for detecting the RF current flowing through the current mirror transistor (T11), wherein said RF detection means (RF-det) is connected to the collector of said first current mirror transistor (T11), and

- a biasing means (bias-RF-det) for biasing said RF detection means (RF-det), wherein said biasing means is connected to said collector of said first current mirror (T11) and said RF detection means (RF-det).

2. Detection circuit according to claim 1, further comprising a DC detector (DC-det) for detecting the DC components of the current flowing through said first current mirror transistor (T11), wherein said DC detector (DC-det) is connected to said collector of said first current mirror transistor (T11).

3. Detection circuit according to claim 1, further comprising:

- a second current mirror transistor (T12) having a base which is connectable to a power transistor (T10), and

- a DC detector (DC-det) for detecting the DC components of the current flowing through said second current mirror transistor (T12), wherein said DC detector (DC-det) is connected to said collector of said second current mirror transistor (T11).

4. Detection circuit according to claim 3, further comprising a RF isolation means (L) connected between the first and second current mirror transistor (T11, T12).

5. Detection circuit according to claim 3 or 4, wherein the detection circuit is implemented on the same chip.